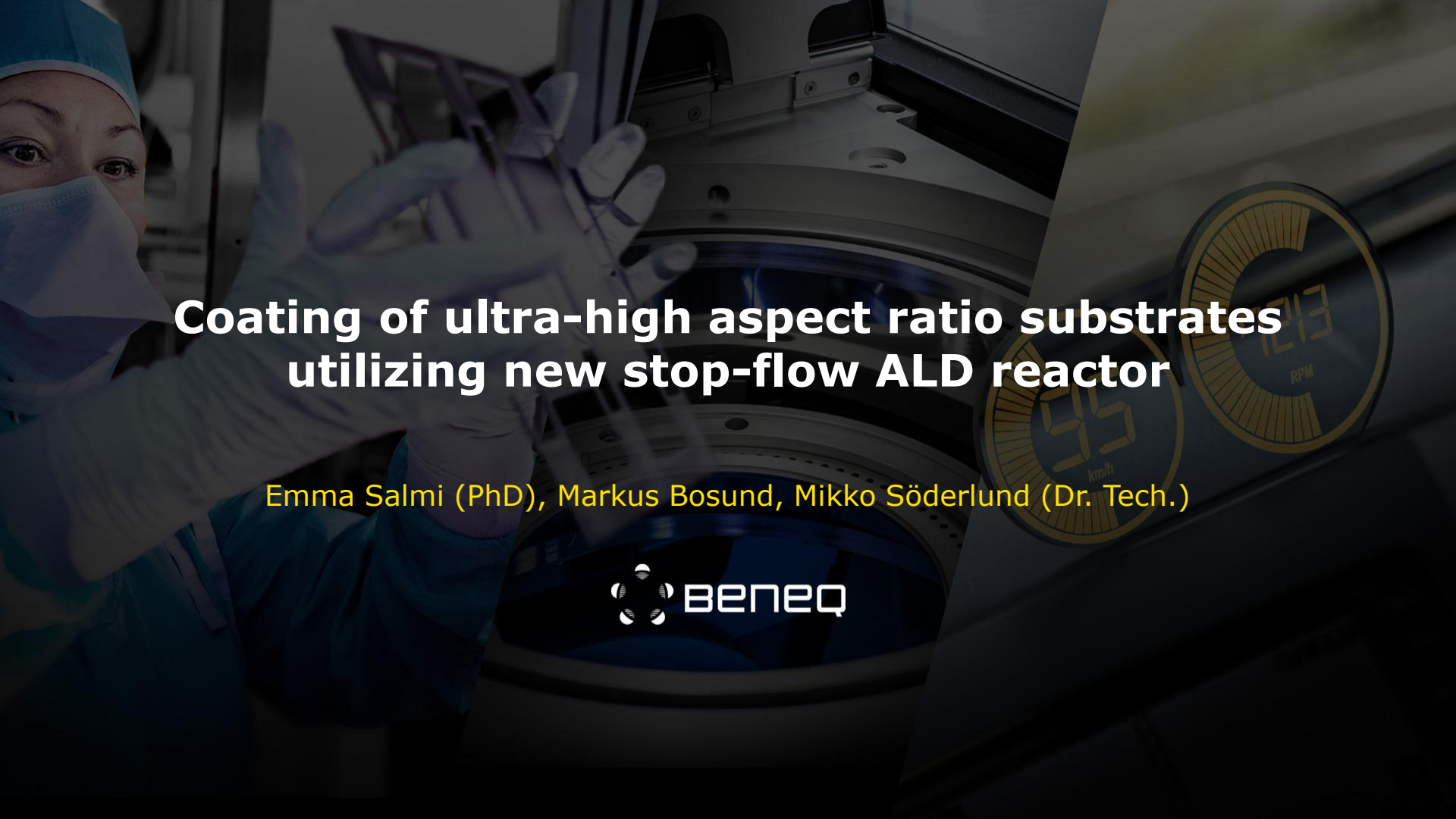




Coating of ultra-high aspect ratio substrates utilizing new stop-flow ALD reactor

Emma Salmi (PhD), Markus Bosund, Mikko Söderlund (Dr. Tech.)





Services

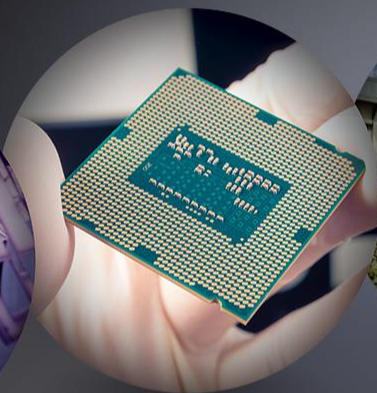
Equipment

Displays

One Stop for All ALD



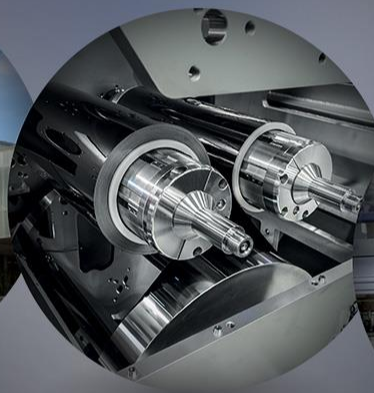
Research



Development
Services



Coating
Services



Industrial
Equipment



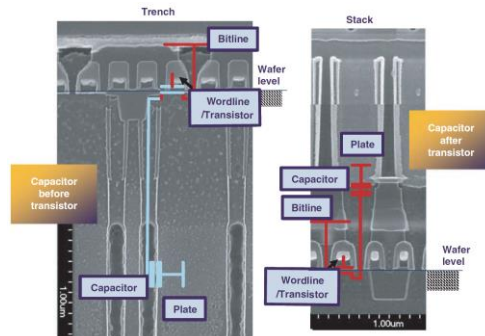
Customer
Services

- Introduction
- Results
 - In-house built test structure
 - Lateral high aspect ratio (LHAR) structure
 - Al_2O_3 on nanotubular TiO_2
- Conclusions

Introduction – Motivation

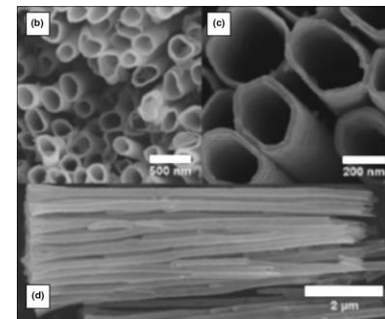
- Conformal thin films in high aspect ratio (AR) structures
 - Atomic layer deposition
 - Increasing demands
 - Higher AR
 - More challenging materials
- New technical solutions needed

Microelectronics



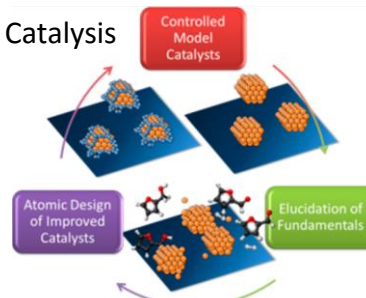
M. Ritala and J. Niinistö, Atomic layer deposition.
In *Chemical Vapour Deposition: Precursors, Processes and Applications*,
A. C. Jones, M. L. Hitchman, Eds.; Royal Society of Chemistry:
Cambridge, U.K., 2009.

Nanofabrication



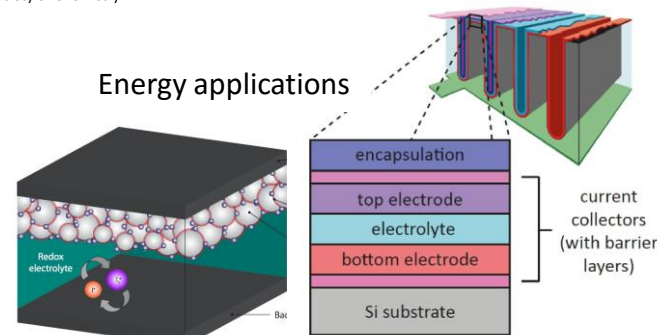
V. Pore et al., J. Am. Chem. Soc. **131** (2009) 3478

Catalysis



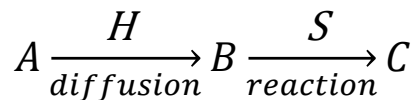
B. J. O'Neill et al. ACS Catal. **5** (2015) 1804-1825.

Energy applications



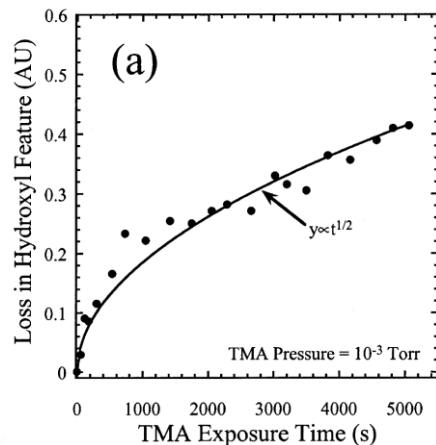
J. A. van Delft et al. Semicond. Sci. Technol. **27** (2012) 074002.

H. Knoop, PhD Thesis, Eindhoven University of Technology, 2011.



$$H = 16 \left(\frac{d}{L} \right)^2$$

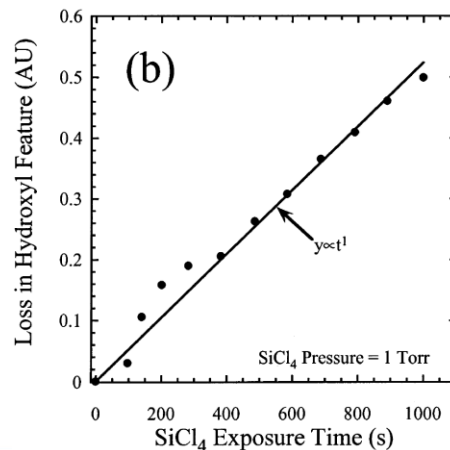
- Diffusion controlled $S \gg H$
 - Reactive sites fill approximately in order from the entrance



$$S_{TMA} = 1 \times 10^{-3}$$

$$H = 1.4 \times 10^{-5}$$

- Reaction controlled $S \ll H$
 - Precursors diffuse along the length of the tube prior to reaction



$$S_{SiCl_4} = 10^{-8}$$

$$H = 1.4 \times 10^{-5}$$

- When the system is diffusion controlled
 - Exposure required to conformally coat a HAR surface

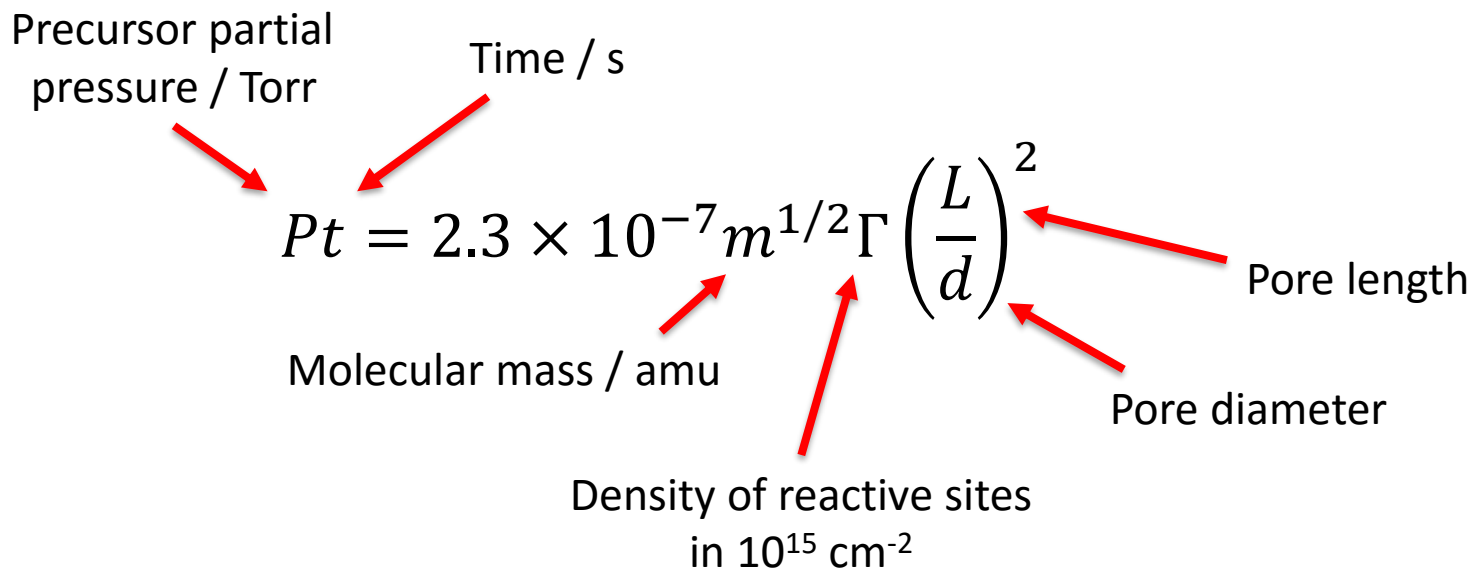


Diagram illustrating the equation for exposure required to conformally coat a HAR surface, showing the relationship between various parameters:

$$Pt = 2.3 \times 10^{-7} m^{1/2} \Gamma \left(\frac{L}{d} \right)^2$$

Parameters and their units:

- Precursor partial pressure / Torr (points to P)
- Time / s (points to t)
- Molecular mass / amu (points to m)
- Density of reactive sites in 10^{15} cm^{-2} (points to Γ)
- Pore length (points to L)
- Pore diameter (points to d)

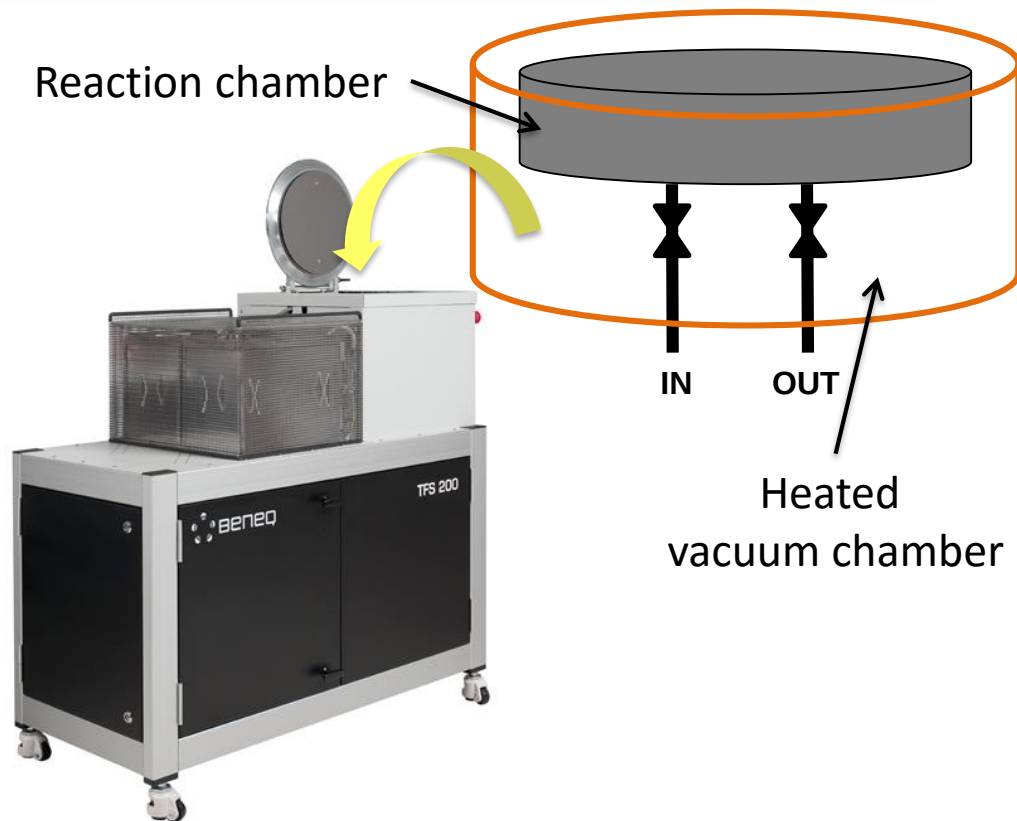
- Comparison of methods used for conformal deposition onto HAR structures

	Constant flow	Reduced flow	Stop-flow
Precursor consumption	High	Intermediate	Low
Conformality in ultra-high AR	Challenging	Enabled	Enabled
Conformality with low sticking coefficient precursors	Challenging	Enabled	Enabled
Control of allowed diffusion time	Challenging	Prolonged, with risk of back diffusion	Full
Pressure	Constant	Increasing	Adjustable

Introduction – The Beneq solution

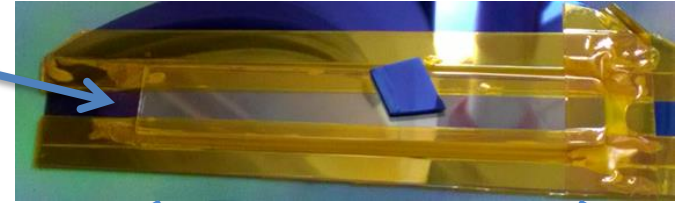


- Beneq HAR module
 - Available for existing and new TFS 200 systems
 - Isothermal conditions
 - Minimum risk of
 - Condensation
 - Powder
 - Leaking valves
 - Temperature specs up to 300 °C
 - Near future upgrade for 450 °C
 - Diffusion (/reaction) time not restricted

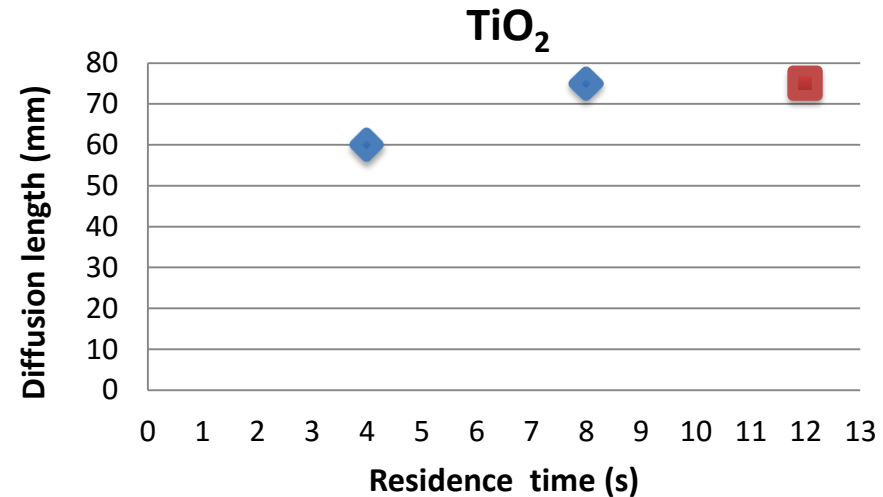
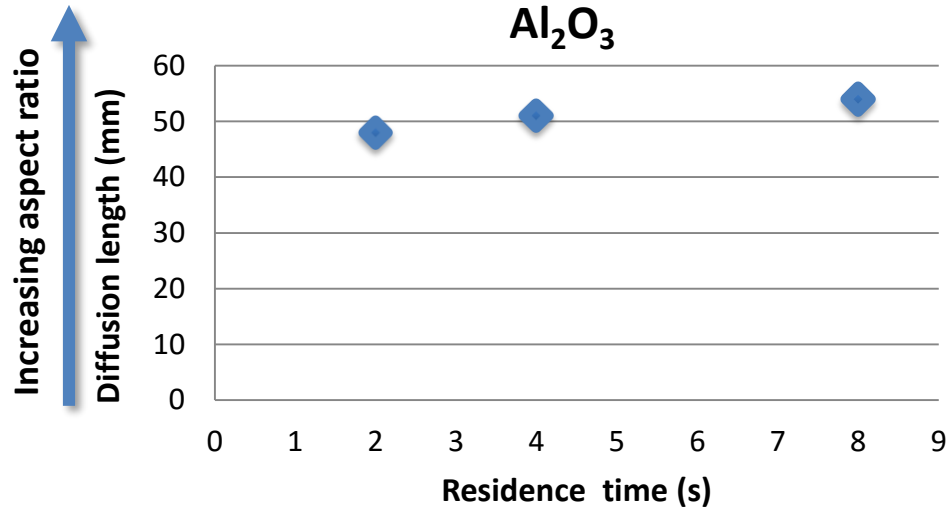


Results – In-house built test structure

62.6 x 1000 μm opening

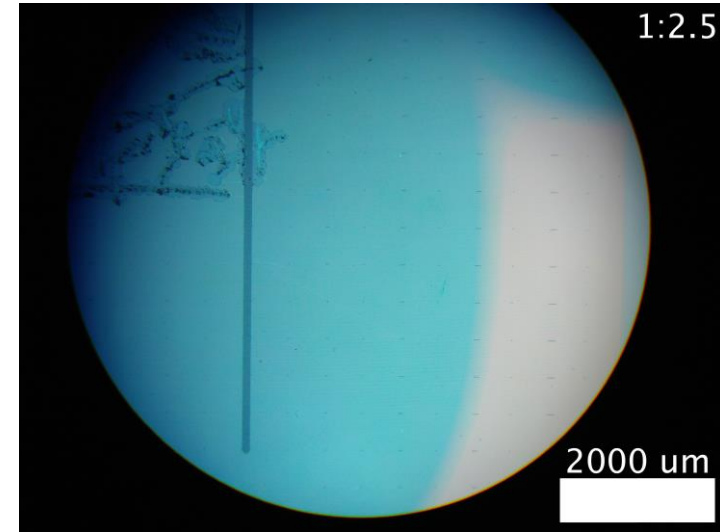
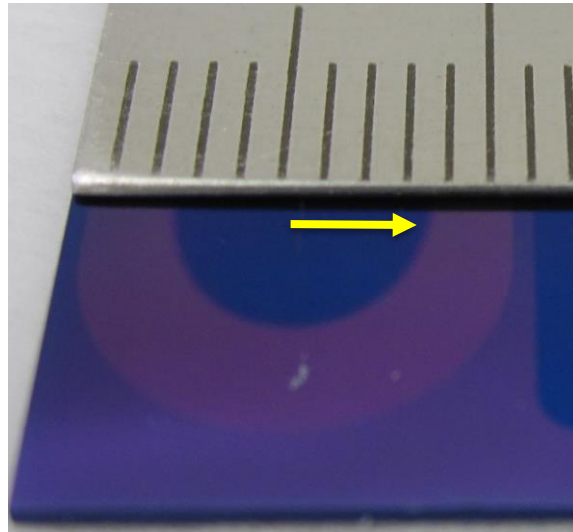
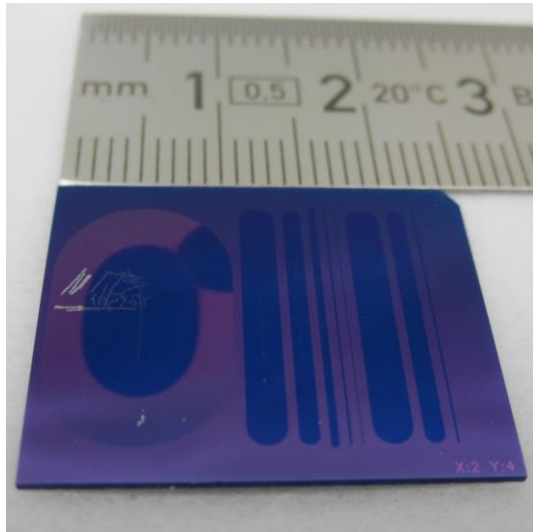
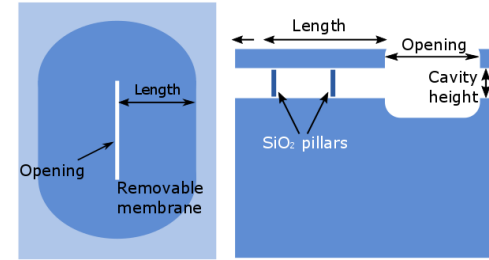


~100 mm length



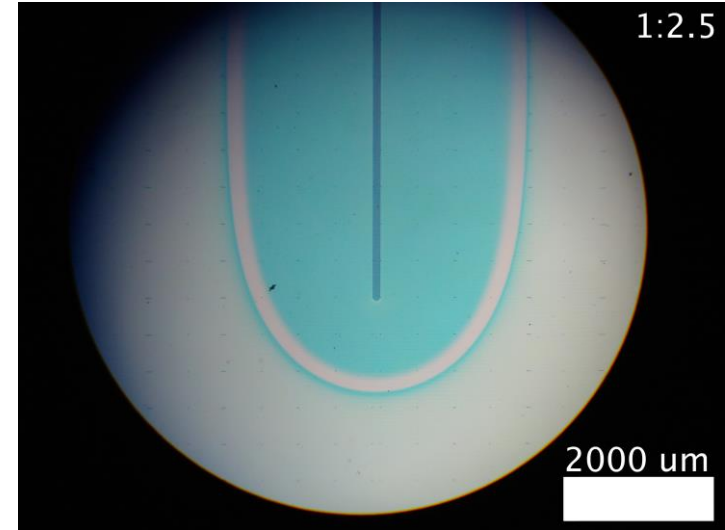
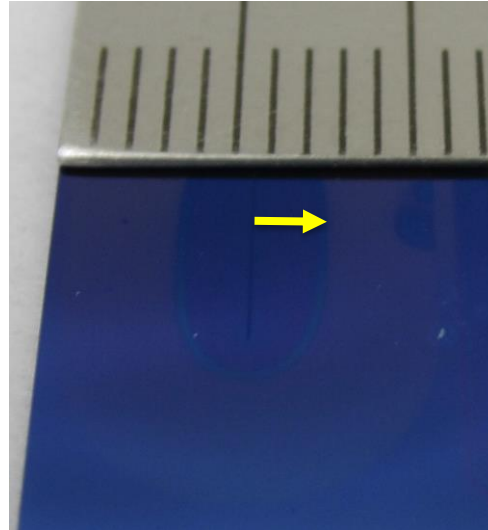
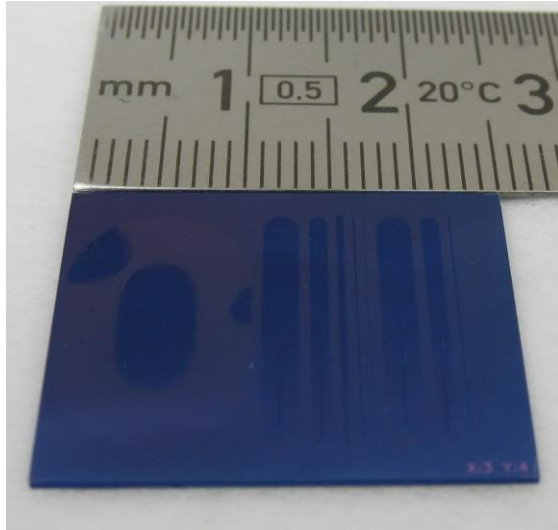
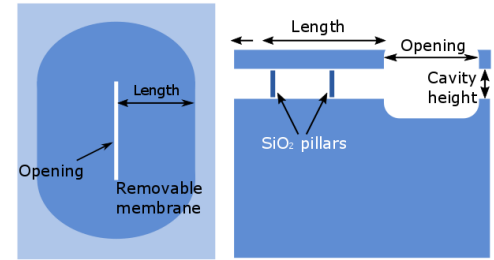
Results – LHAR structure

- Al_2O_3
 - Growth up to 3000 μm length
→ Aspect ratio 1:3000

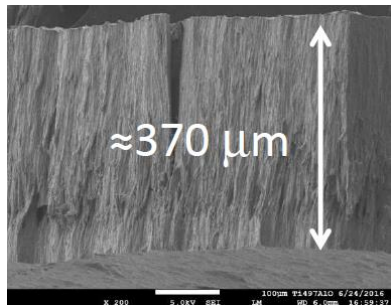


Results – LHAR structure

- TiO_2
 - Growth up to 2000 μm length
→ Aspect ratio 1:2000



Results –Al₂O₃ on nanotubular TiO₂

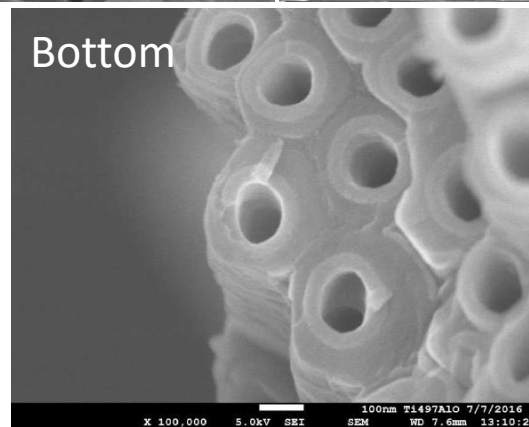
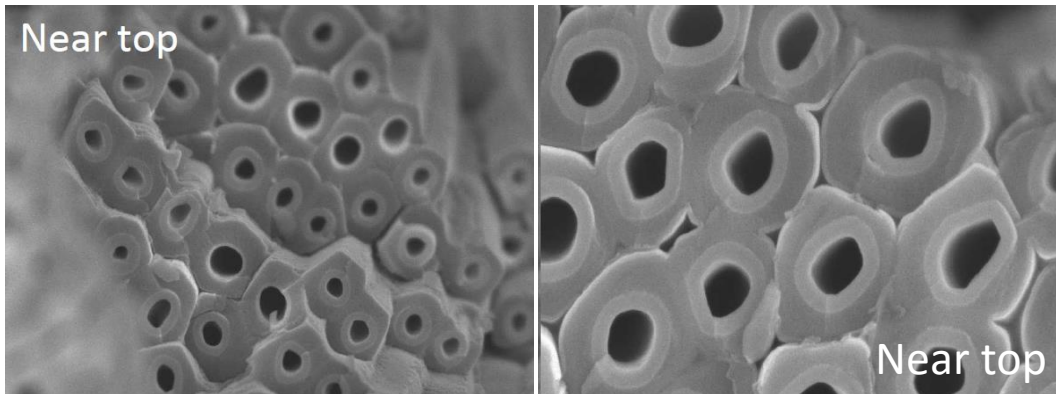


Bottom diameter
 170.7 ± 27.8 nm

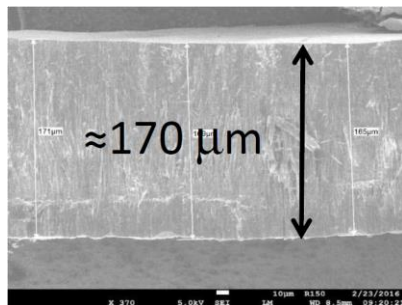
Aspect ratio 1:1088

Thickness

- Middle 38.8 ± 4.0 nm
- Bottom 39.8 ± 5.7 nm



Results –Al₂O₃ on nanotubular TiO₂

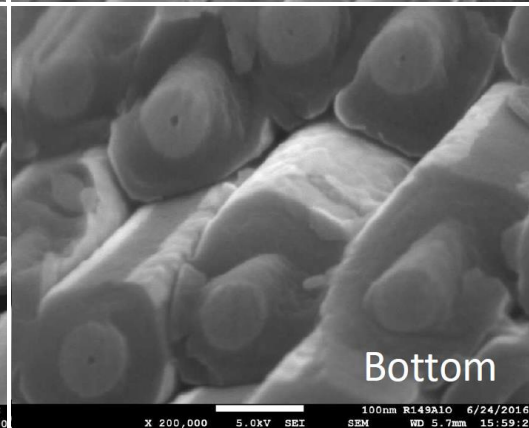
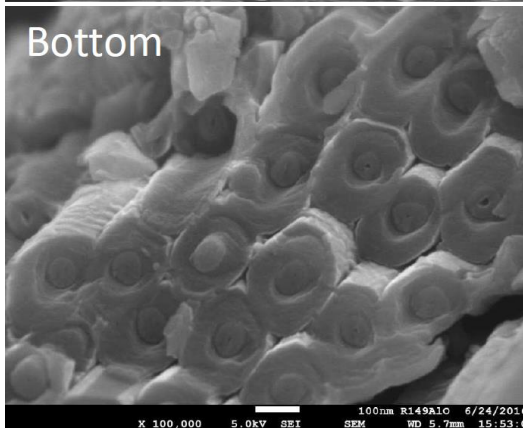
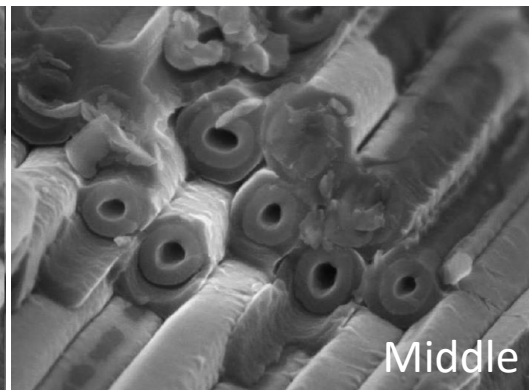
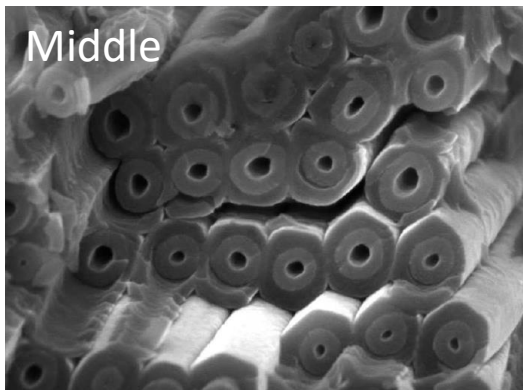


Bottom diameter
 $76.9 \pm 5.2 \text{ nm}$

Aspect ratio 1:1105

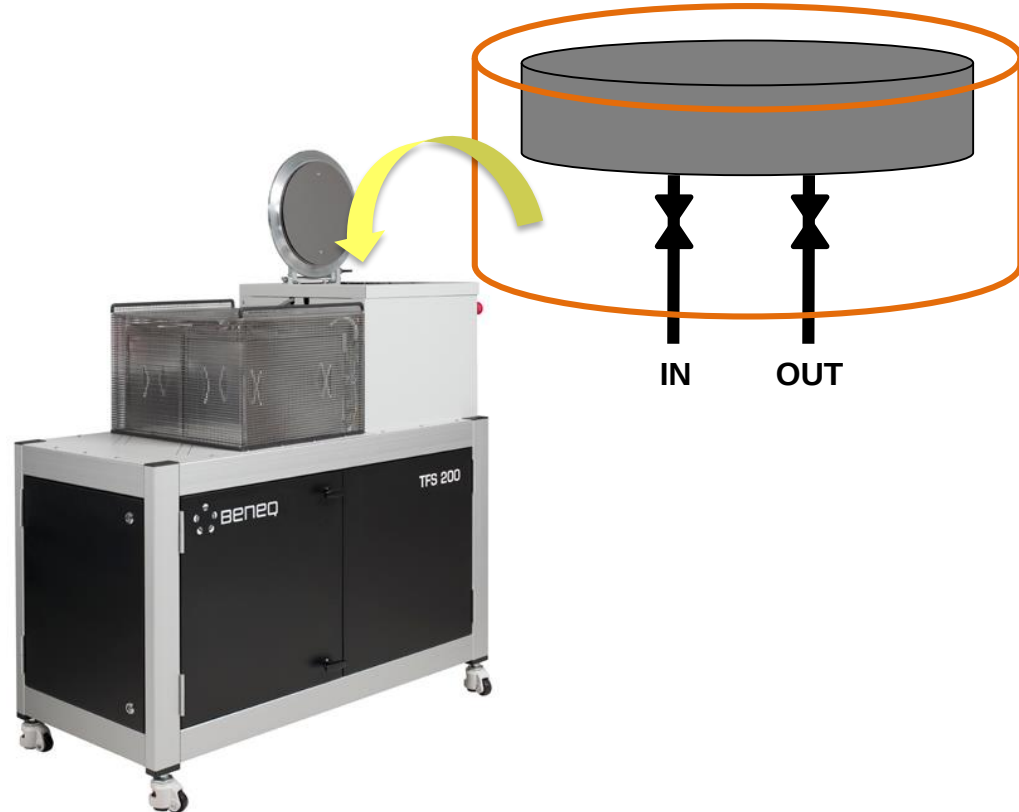
Thickness

- Middle $34.2 \pm 3.6 \text{ nm}$
- Bottom $35.5 \pm 2.5 \text{ nm}$



Conclusions

- Stop-flow
 - Conformal ALD enabled into ultra-high AR structures
 - Problems with continuous flow and reduced flow solved
- Beneq HAR module available for existing and new TFS 200 systems
 - Isothermal conditions
 - Temp up to 300 °C
 - Proven performance to AR 1:3000





Thank you

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emma.salmi@beneq.com

